

Title (en)
CHARGE SENSOR

Publication
EP 0155023 B1 19900425 (EN)

Application
EP 85200165 A 19850211

Priority
NL 8400453 A 19840213

Abstract (en)
[origin: EP0155023A1] The invention relates to a charge detector, more particularly for reading binary information in a CTD. The detector in principle consists of a flipflop having two cross-coupled MOS transistors and two MOS transistors acting as loads. The signal to be read and the reference signal are supplied to the gates of the loads. The junctions between the driver transistors and the loads are connected to reset transistors. The drains of the loads are applied to a (fixed) supply voltage and the sources of the driver transistors are applied via a switching transistor to the other supply voltage. The circuit arrangement is operated so that before the activation of the flipflop the said junctions are set to a signal-dependent preadjustment. When the switching transistor is then energized, the flipflop will occupy the correct stage with a higher degree of reliability and without being influenced by clock cross-talk.

IPC 1-7
G11C 19/28

IPC 8 full level
G11C 27/04 (2006.01); **G11C 19/28** (2006.01)

CPC (source: EP US)
G11C 19/285 (2013.01 - EP US)

Citation (examination)
• US 3983413 A 19760928 - GUNSAGAR KAMLESHWAR C, et al
• US 4131951 A 19781226 - ASAHI HIROJI

Cited by
KR101131916B1

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EP 0155023 A1 19850918; EP 0155023 B1 19900425; DE 3577368 D1 19900531; JP S60187999 A 19850925; NL 8400453 A 19850902; US 4695753 A 19870922

DOCDB simple family (application)
EP 85200165 A 19850211; DE 3577368 T 19850211; JP 2508685 A 19850212; NL 8400453 A 19840213; US 91024786 A 19860918